

Inchange Semiconductor

Product Specification

Silicon NPN Power Transistors

2SC2122

DESCRIPTION

- With TO-3 package
- Short switching times.
- High dielectric strength.

APPLICATIONS

- For use in TV horizontal deflection stage

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

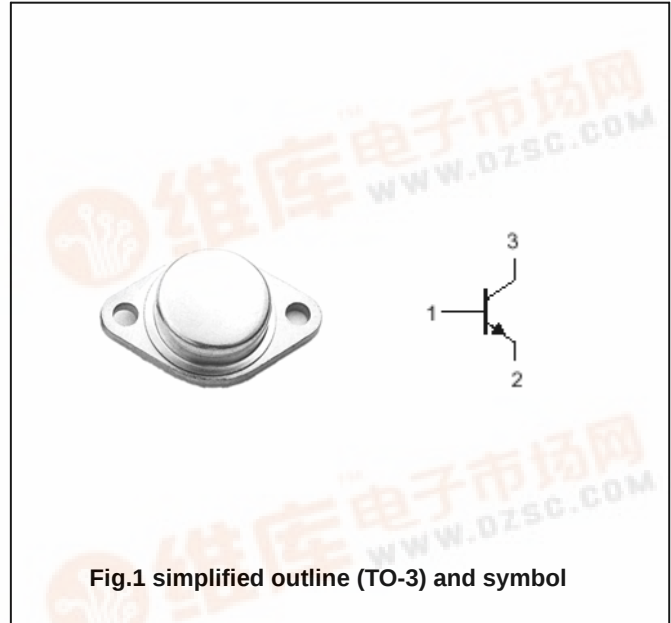


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a = ^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	800	V
V_{CEO}	Collector-emitter voltage	Open base	325	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		10	A
P_T	Total power dissipation	$T_C = 25^\circ\text{C}$	50	W
T_j	Junction temperature		175	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~175	$^\circ\text{C}$

Silicon NPN Power Transistors**2SC2122****CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=50mA; I_B=0;$	325			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1mA; I_C=0;$	7			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=8A; I_B=2.5 A$			3.3	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=8A; I_B=2.5 A$			2.2	V
I_{CBO}	Collector cut-off current	$V_{CB}=800V; I_E=0$			1.0	mA
I_{EBO}	Emitter cut-off current	$V_{EB}=7V; I_C=0$			1.0	mA
h_{FE}	DC current gain	$I_C=2.5A; V_{CE}=10V$	15			
f_T	Transition frequency	$I_C=0.1A; V_{CE}=10V$		6		MHz

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PACKAGE OUTLINE

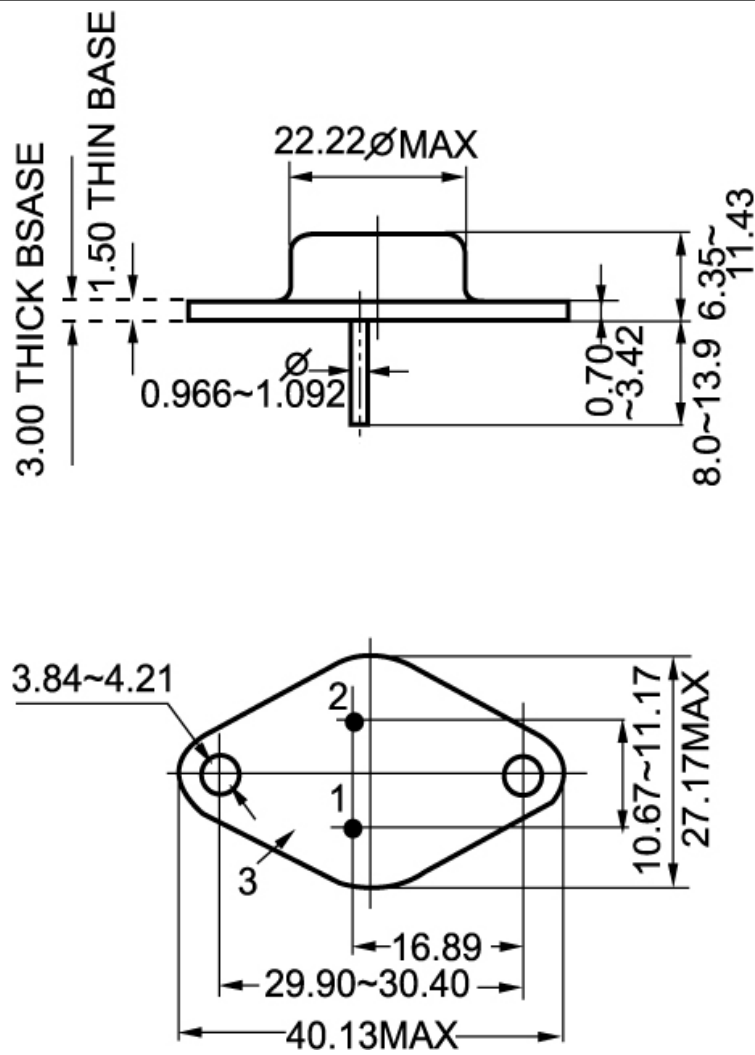


Fig.2 Outline dimensions